

20V,5A N-Channel Mosfet

FEATURES

RDS(ON)≤ 25m Ω @VGS=4.5V

RDS(ON)≤ 38m Ω @VGS=2.5V

APPLICATIONS

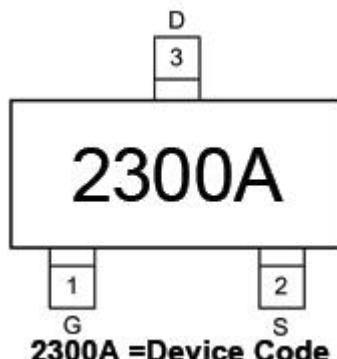
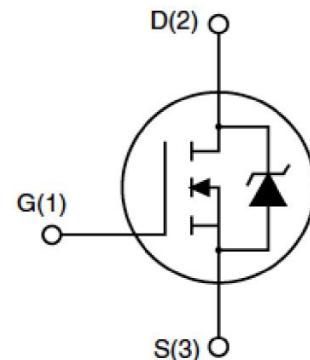
PWM Applications

Load Switch

Power Management

PACKAGE

SOT-23

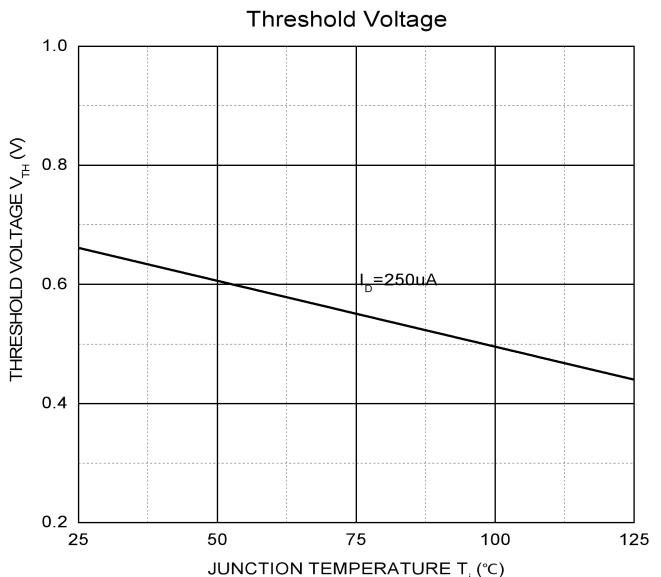
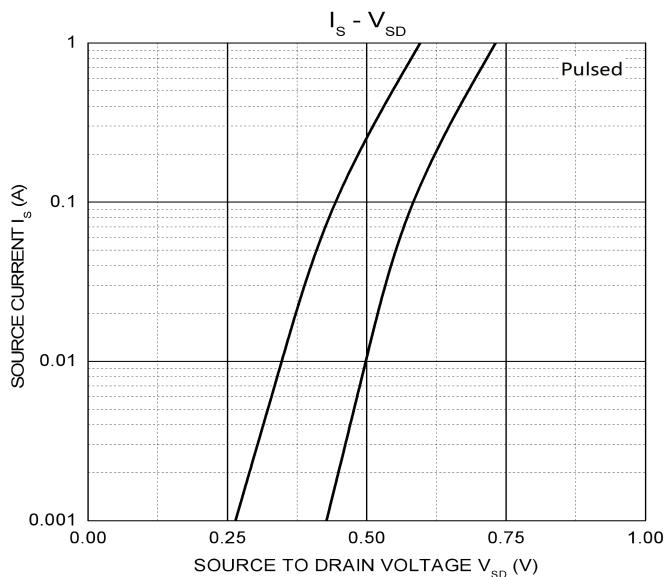
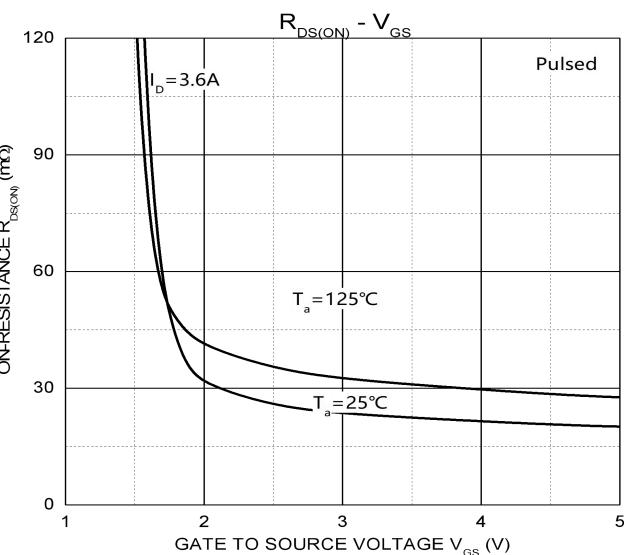
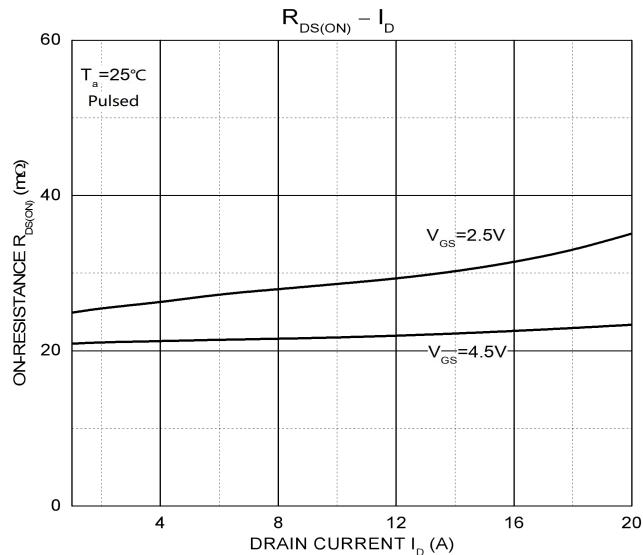
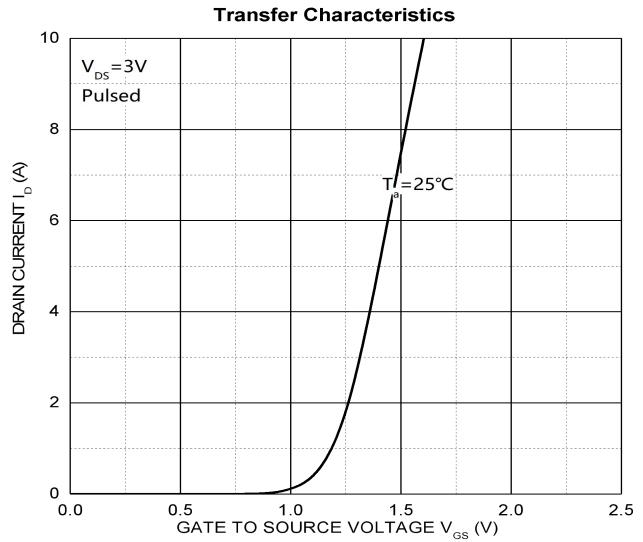
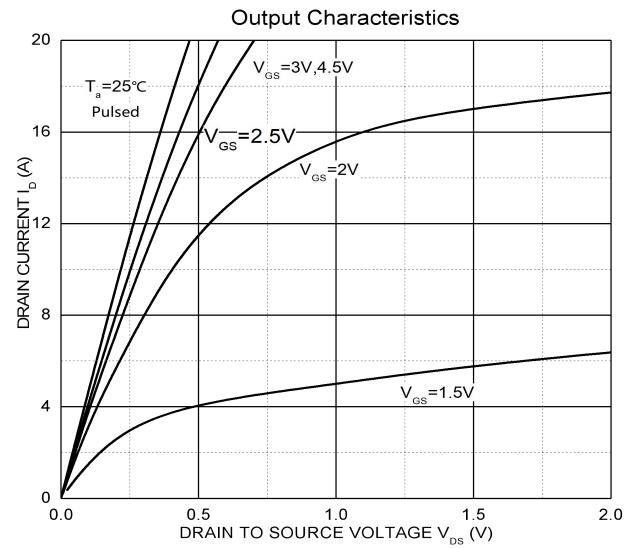
MARKING**N-CHANNEL MOSFET****Absolute maximum ratings (Ta=25°C unless otherwise noted)**

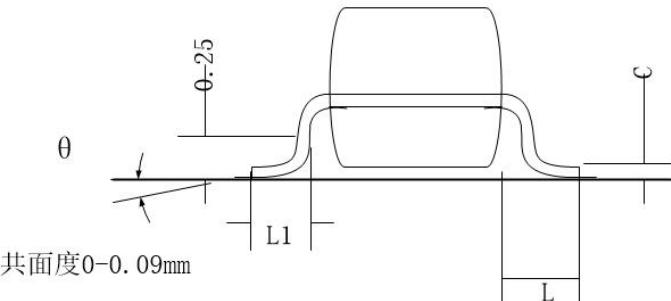
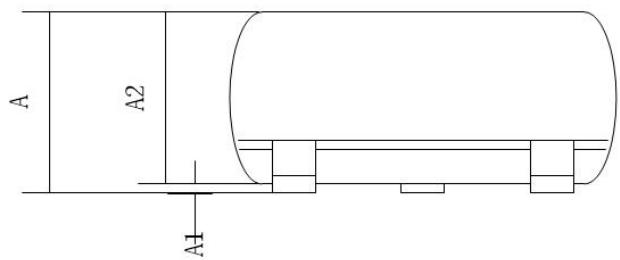
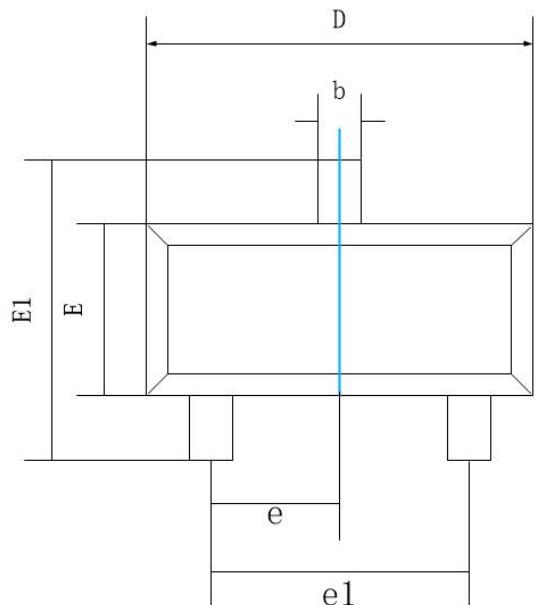
| Parameter | Symbol | Value | Unit |
|---|------------------|-----------|------|
| Drain-Source Voltage | V _{DS} | 20 | V |
| Gate-Source Voltage | V _{GS} | ±12 | V |
| Continuous Drain Current | I _D | 5 | A |
| Plused Drain Current | I _{DM} | 25 | A |
| Power Dissipation | P _D | 0.35 | W |
| Thermal Resistance from Junction to Ambient | R _{θJA} | 357 | °C/W |
| Junction Temperature | T _J | 150 | °C |
| Storage Temperature | T _{STG} | -55~ +150 | °C |

Electrical characteristics ($T_A=25^\circ\text{C}$, unless otherwise noted)

| Parameter | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|----------------------------------|-----------------------------|--|------|------|-----------|------------------|
| Static Characteristics | | | | | | |
| Drain-source breakdown voltage | $V_{(\text{BR})\text{DSS}}$ | $V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$ | 20 | | | V |
| Zero gate voltage drain current | I_{DSS} | $V_{\text{DS}} = 20\text{V}, V_{\text{GS}} = 0\text{V}$ | | | 1 | μA |
| Gate-body leakage current | I_{GSS} | $V_{\text{GS}} = \pm 12\text{V}, V_{\text{DS}} = 0\text{V}$ | | | ± 0.1 | μA |
| Gate threshold voltage | $V_{\text{GS}(\text{th})}$ | $V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$ | 0.5 | 0.66 | 1.2 | V |
| Drain-source on-resistance | $R_{\text{DS}(\text{on})}$ | $V_{\text{GS}} = 4.5\text{V}, I_D = 4.5\text{A}$ | | 20 | 25 | $\text{m}\Omega$ |
| | | $V_{\text{GS}} = 2.5\text{V}, I_D = 3.5\text{A}$ | | 25 | 38 | |
| Diode forward voltage | V_{SD} | $I_S = 1.7\text{A}, V_{\text{GS}} = 0\text{V}$ | | | 1.2 | V |
| Dynamic characteristics | | | | | | |
| Total gate charge | Q_g | $V_{\text{DS}} = 10\text{V}, V_{\text{GS}} = 4.5\text{V}, I_D = 4\text{A}$ | | 11 | | nC |
| Gate-source charge | Q_{gs} | | | 2.3 | | |
| Gate-drain charge | Q_{gd} | | | 2.5 | | |
| Input Capacitance | C_{iss} | $V_{\text{DS}} = 8\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$ | | 800 | | pF |
| Output Capacitance | C_{oss} | | | 155 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 125 | | |
| Switching Characteristics | | | | | | |
| Turn-on delay time | $t_{\text{d}(\text{on})}$ | $V_{\text{DD}} = 10\text{V}, V_{\text{GS}} = 4\text{V}, I_D = 1\text{A}$ $R_G = 10\Omega$ | | 18 | | ns |
| Turn-on rise time | t_r | | | 5 | | |
| Turn-off delay time | $t_{\text{d}(\text{off})}$ | | | 43 | | |
| Turn-off fall time | t_f | | | 20 | | |

Typical Characteristics



SOT-23 Package Information

| Symbol | Dimensions In Millimeters | |
|--------|---------------------------|------|
| | Min. | Max. |
| A | 0.90 | 1.15 |
| A1 | 0.00 | 0.10 |
| A2 | 0.90 | 1.05 |
| b | 0.30 | 0.50 |
| c | 0.08 | 0.15 |
| D | 2.80 | 3.00 |
| E | 1.20 | 1.40 |
| E1 | 2.25 | 2.55 |
| e | 0.95 REF. | |
| e1 | 1.80 | 2.00 |
| L | 0.55 REF. | |
| L1 | 0.30 | 0.50 |
| θ | 0° | 8° |